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		FILING DATE December 7, 2001	GROUP Unassigned	

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
SBG	AM	110003990	1/6/99	JAPAN	—	—	✗
	AN						
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SBG	AU	1998 International Electron Device Meeting Technical Digest, (Pgs. 1038-1040), A 1.1 nm Oxide Equivalent Gate Insulator Formed Using TiO ₂ on Nitrided Silicon.
SBG	AV	IEEE Transactions on Electron Devices, Vol. 46, No. 7, July 1999, (Pages 1537-1544). The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's
	AW	
	AX	
	AY	
	AZ	

Examiner	<i>Det. B. Ay</i>	Date Considered 4-15-03
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